



V. 구두발표

D. Thin Film Process Technology 분과

2021년 1월 25일(월), 09:00-10:30 / 채널 A

[MA1-D] Ferroelectric Films I

좌장: 김성근 박사 (KIST), 이웅규 교수 (명지대학교)

<p>MA1-D-1 09:00-09:15</p>	<p>고농도 P 도핑 Si 박막 표면에서 엑스선 광전자 분광법을 이용한 전기적으로 활성화 된 P 원자의 화학적 결합 특성 분석 류화연, 신현수, 고대홍 연세대학교 신소재공학과</p>
<p>MA1-D-2 09:15-09:30</p>	<p>Investigation on Interfacial Charge Compensation of HZO-based MFIS Capacitors for Enhanced Memory Window Yong Bin Lee^{1,2}, Hyeon Woo Park^{1,2}, Seung Dam Hyun^{1,2}, Beom Yong Kim^{1,2}, Suk Hyun Lee^{1,2}, Minsik Oh^{1,2}, Seung Kyu Ryu^{1,2}, In Soo Lee^{1,2}, Seung Ryong Byun^{1,2}, Soo Jin Jo^{1,2}, Do Sup Shim^{1,2}, and Cheol Seong Hwang^{1,2} ¹Department of Materials Science and Engineering, Seoul National University, ²Inter-University Semiconductor Research Center, Seoul National University</p>
<p>MA1-D-3 09:30-09:45</p>	<p>Effect of Defects on Ferroelectricity in Hafnia Based Thin Films Dong Hyun Lee, Kun Yang, Ju Yong Park, and Min Hyuk Park School of Materials Science and Engineering, Pusan National University</p>
<p>MA1-D-4 09:45-10:00</p>	<p>Ferroelectric Al-doped HfO₂ Thin Film Transistors for Analog Synaptic Device Duho Kim, Boncheol Ku, Tae Hun Kim, and Changhwan Choi Division of Materials Science & Engineering, Hanyang University</p>
<p>MA1-D-5 10:00-10:15</p>	<p>Investigation on Ferroelectric Polarization Switching Kinetics of Al-doped HfO₂ Thin Films Deposited with ALD Using H₂O as Oxygen Source Jin-Ju Kim and Sung-Min Yoon Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</p>
<p>MA1-D-6 10:15-10:30</p>	<p>Ferroelectric Properties of Hf_{1-x}Zr_xO₂ Thin Films Deposited by Atomic Layer Deposition Using Cyclopentadienyl Cocktail-precursor Without Annealing Process Hyo-Bae Kim¹, Moonyoung Jung², Seung Won Lee¹, Dongseok Suh², and Ji-Hoon Ahn¹ ¹Department of Materials Science and Chemical Engineering, Hanyang University, ²Department of Energy Science, Sungkyunkwan University</p>